

## Supplementary Information

### Two-Dimensional SnS<sub>2</sub> Nanosheets as Electron Transport and Interfacial Layers Enable Efficient Perovskite Solar Cells

Yichuan Rui<sup>a,\*</sup>, Tianpeng Li<sup>a</sup>, Bin Li<sup>a</sup>, Yuanqiang Wang<sup>a</sup>, Peter Müller-Buschbaum<sup>b,c</sup>

<sup>a</sup>*College of Chemistry and Chemical Engineering, Shanghai University of  
Engineering Science, Shanghai 201620, P. R. China*

<sup>b</sup>*Lehrstuhl für Funktionelle Materialien, Physik-Department, Technische Universität  
München, Jams-Franck-Strasse 1, 85748 Garching, Germany*

<sup>c</sup>*Heinz Maier-Leibnitz Zentrum (MLZ), Technische Universität München,  
Lichtenbergstr. 1, 85748 Garching, Germany*

\*E-mail: ryc713@126.com

#### 1. Characterization

The morphologies of the films and devices were characterized by a field-emission scanning electron microscope (FESEM) (SU8010, Hitachi, Japan) and transmission electron microscope (TEM) (2100F, JEOL, Japan). AFM images were characterized by an atomic force microscope (Dimension, Germany Bruker). X-ray diffraction (XRD) spectra were measured by using a Rigaku D/Max 2550 V X-ray diffractometer with Cu K $\alpha$  ( $\lambda = 0.154$  nm) radiation. The infrared spectra were performed by Fourier transform infrared spectrometer (PerkinElmer, USA). The transmittance and absorption spectra were performed using a Lambda 950UV-vis spectrophotometer (PerkinElmer, USA). X-ray photoelectron spectroscopy (XPS) and Ultraviolet photoelectron spectroscopy (UPS) were measured by an Escalab 250Xi XPS system (Thermo Scientific, USA). Steady-state photo-luminescence (PL) and time-resolved photoluminescence (TRPL) were performed by using a FLS920 transient optical spectrometer (Edinburgh Instruments, UK). The photocurrent density-voltage (J-V) curves were performed by a digital source meter analyzer (Keithley 2400) under AM 1.5G with the light intensity calibrated to 100 mW cm<sup>-2</sup>. Electrochemical impedance spectroscopy (EIS) was acquired with a Zahner-elektrik (Germany) workstation. The PSCs were masked using a shadow metal mask to limit the active cell area to 0.16 cm<sup>2</sup>.

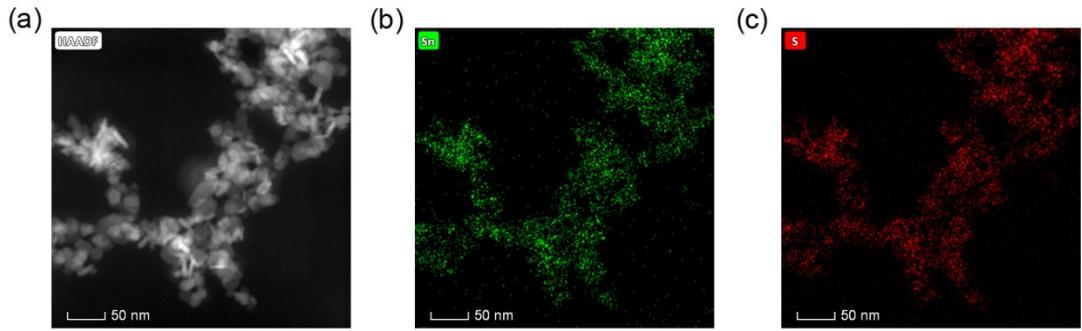


Fig. S1 (a) High-angle annulus dark field TEM image of NS-1 SnS<sub>2</sub> nanosheets, and the EDS mapping of (b) Sn and (c) S elements.

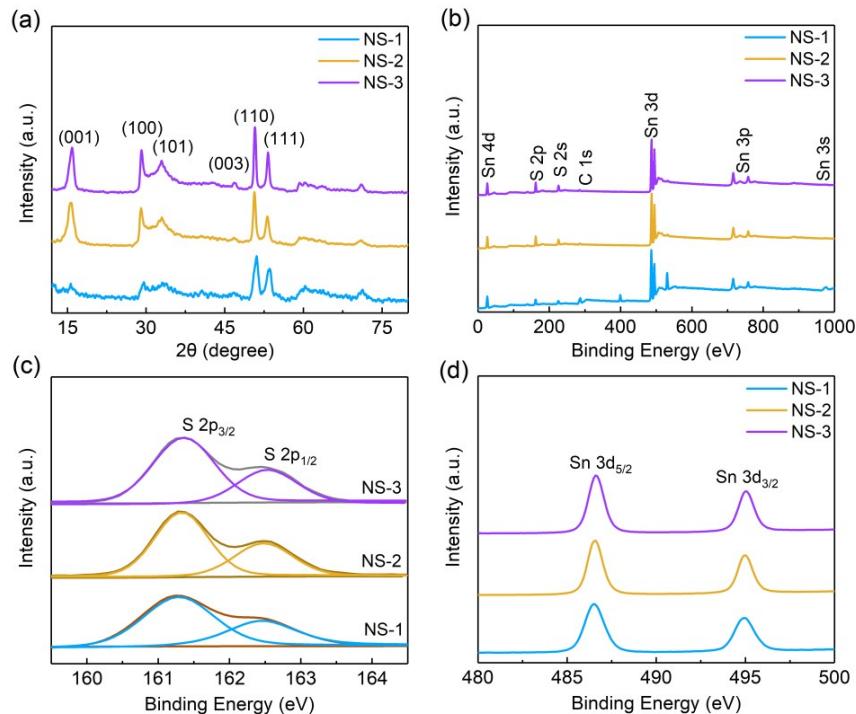


Fig. S2 (a) XRD, (b) XPS survey, (c) S 2p and (d) Sn 3d spectra of the SnS<sub>2</sub> ETLs.

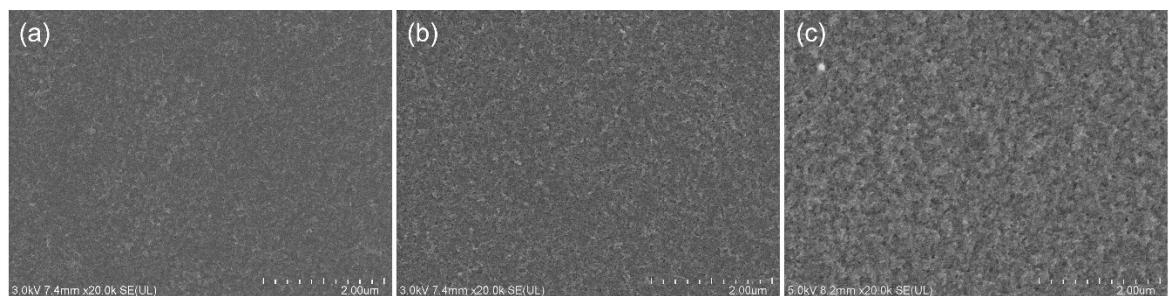


Fig. S3 Top-view SEM images of SnS<sub>2</sub> ETLs: (a) NS-1, (b) NS-2 and (c) NS-3.

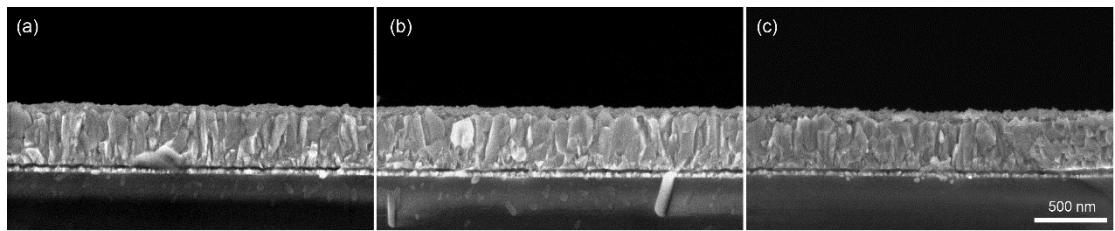


Fig. S4 Cross-sectional SEM images of SnS<sub>2</sub> ETLs: (a) NS-1, (b) NS-2 and (c) NS-3.

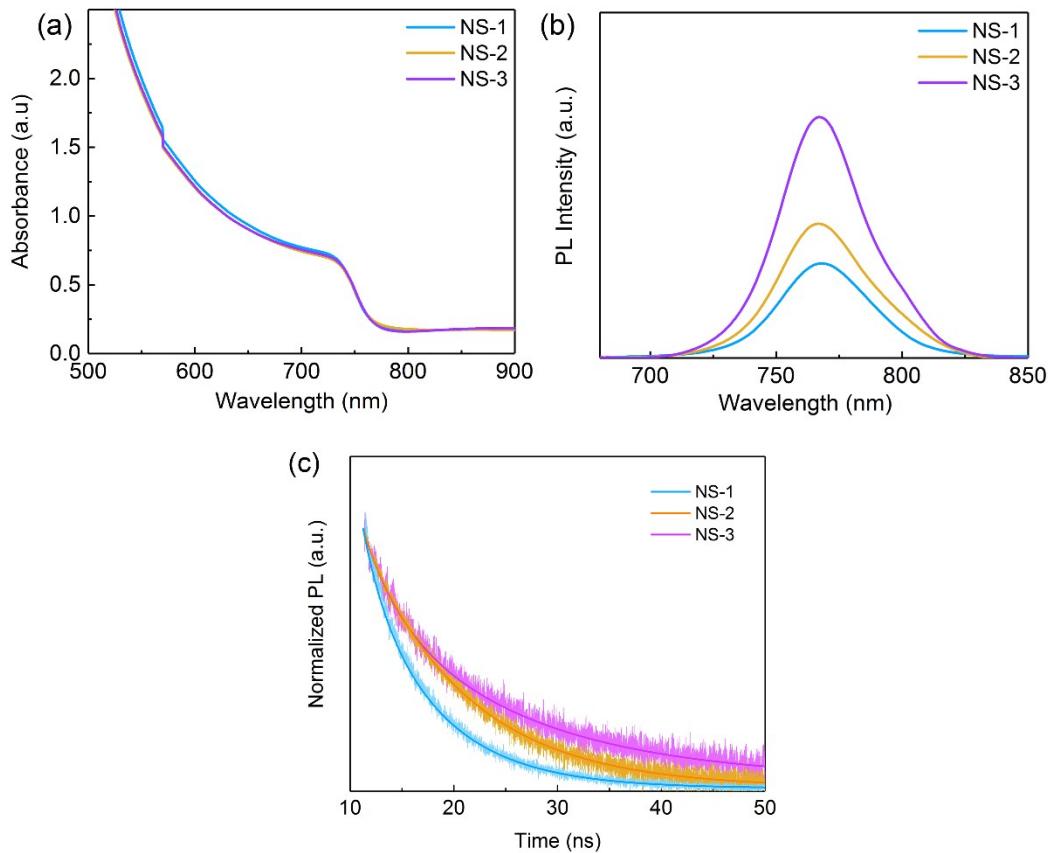


Fig. S5 (a) Absorbance spectra, (b) steady-state PL and (c) TRPL spectra of FTO/NS-1/perovskite, FTO/NS-2/perovskite and FTO/NS-3/perovskite.

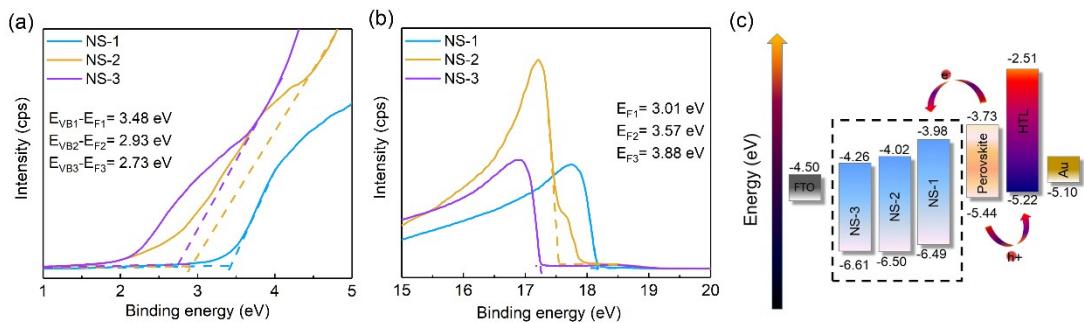


Fig. S6 (a) Valence band region and (b) secondary-electron cut-off of the  $\text{SnS}_2$  films.

(c) The energy level diagram of the devices.

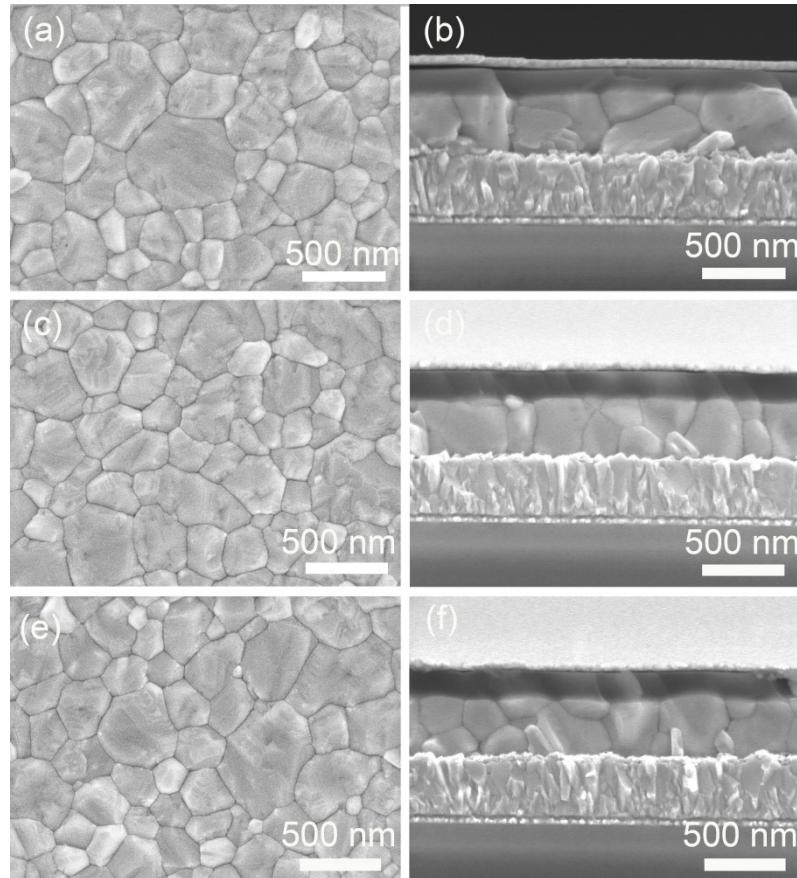


Fig. S7 (a,c,d) Surface and (b,d,f) cross-sectional SEM images of perovskite films based on different ETLs: (a,b) NS-1, (c,d) NS-2, (e,f) NS-3.

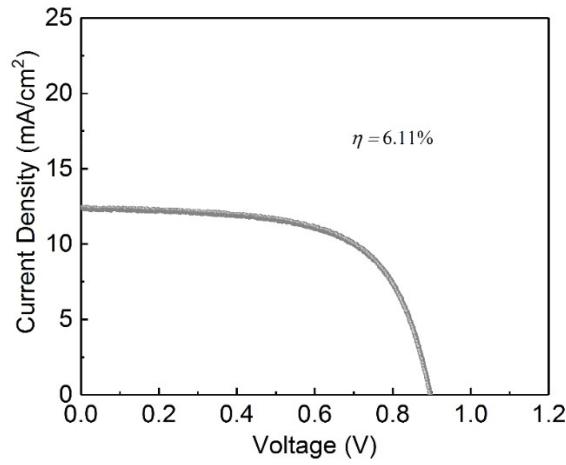


Fig. S8 The J-V curve of PSCs without ETLs.

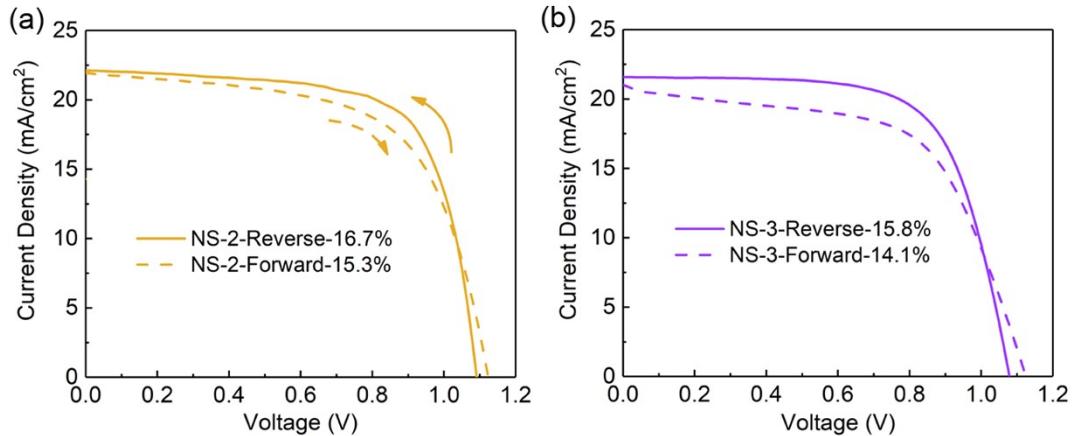


Fig. S9 The J-V curves of (a) NS-2 and (b) NS-3 PSCs under reverse and forward scan.

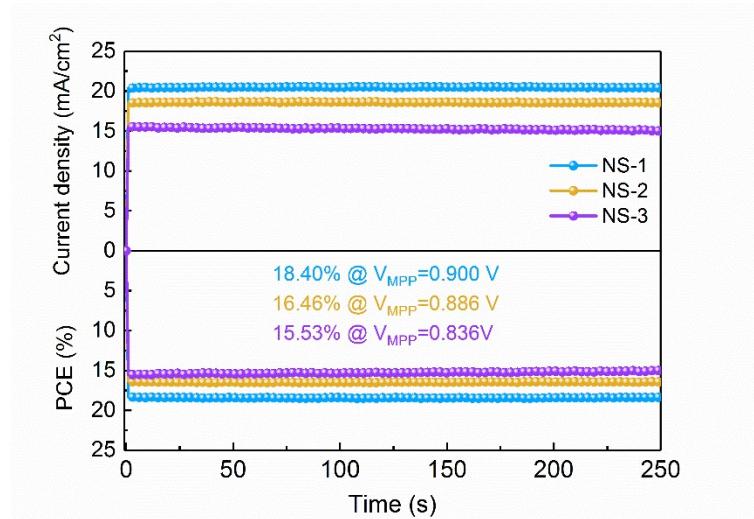


Fig. S10 Stabilized current density and PCE of PSCs at maximum power point.

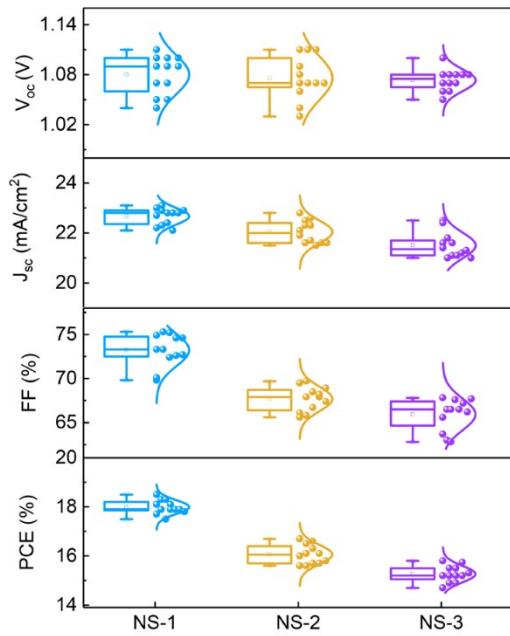


Fig. S11 Statistics of the photovoltaic parameters of the PSCs based on NS-1, NS-2, NS-3.

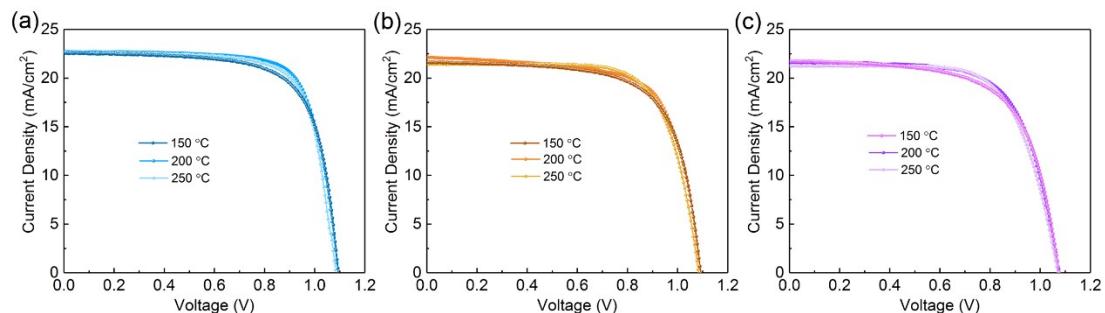


Fig. S12 The J-V curves of PSCs based on different annealing temperature: (a) NS-1, (b) NS-2 and (c) NS-3

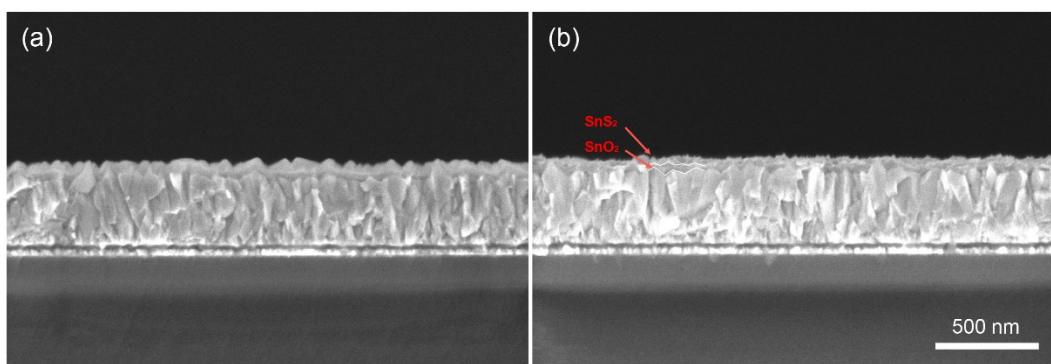


Fig. S13 Cross-sectional SEM images of (a) SnO<sub>2</sub> and (b) SnO<sub>2</sub>-SnS<sub>2</sub> ETLs.

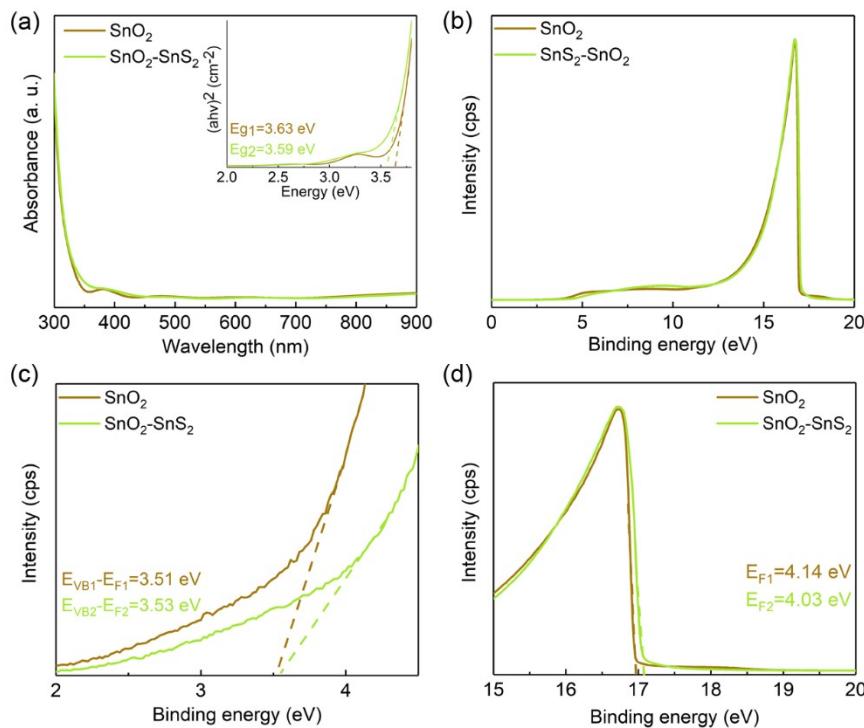


Fig. S14 (a) UV-vis absorbance spectra and the corresponding Tauc plot (inset). (b) UPS spectra. (c) Valence band region and (d) secondary-electron cut-off.

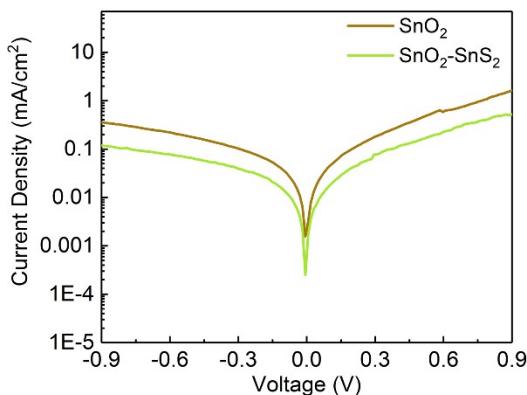


Fig. S15 Dark current-voltage responses of  $\text{SnO}_2$  and  $\text{SnO}_2\text{-SnS}_2$  PSCs.

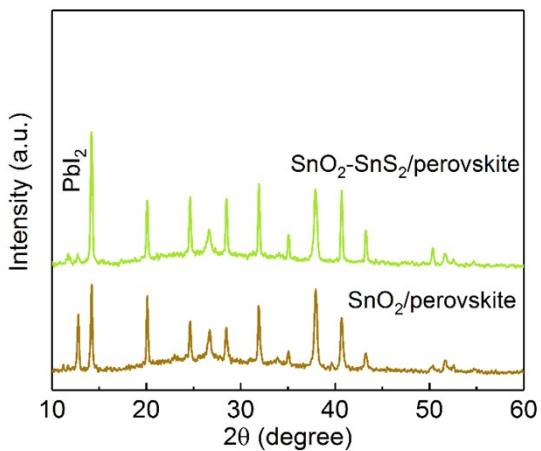


Fig. S16 XRD of perovskites prepared on  $\text{SnO}_2$  and  $\text{SnO}_2\text{-}\text{SnS}_2$  ETLs stored in air atmosphere for 14 days (relative humidity 40~50%).

Table S1. Photovoltaic parameters of PSCs based on different annealing temperature.

| Samples |        | $V_{oc}$ (V) | $J_{sc}$ (mA/cm <sup>2</sup> ) | FF (%) | PCE (%) |
|---------|--------|--------------|--------------------------------|--------|---------|
| NS-1    | 150 °C | 1.09         | 22.5                           | 71.3   | 17.6    |
|         | 200 °C | 1.09         | 22.7                           | 74.9   | 18.5    |
|         | 250 °C | 1.08         | 22.6                           | 73.9   | 18.2    |
| NS-2    | 150 °C | 1.09         | 21.6                           | 68.7   | 16.3    |
|         | 200 °C | 1.09         | 22.1                           | 69.5   | 16.7    |
|         | 250 °C | 1.08         | 21.5                           | 71.5   | 16.6    |
| NS-3    | 150 °C | 1.08         | 21.7                           | 65.1   | 15.2    |
|         | 200 °C | 1.08         | 21.6                           | 67.8   | 15.8    |
|         | 250 °C | 1.07         | 21.2                           | 68.5   | 15.6    |

Table S2 The trap-filled limit voltage and trap-state density of the devices based on different  $\text{SnS}_2$  ETLs.

| Sample                                       | NS-1 | NS-2 | NS-3 |
|--|------|------|------|
| $V_{TFL}$ (V)                                | 0.42 | 0.44 | 1.24 |
| Trap densities ( $10^{16} \text{ cm}^{-3}$ ) | 0.87 | 0.91 | 2.57 |

Table S3 Fit data from TRPL curves.

| Sample   | $\tau_1$ (ns) | A <sub>1</sub> | $\tau_2$ (ns) | A <sub>2</sub> | $\tau_{avg.}$ (ns) |
|--|---------------|----------------|---------------|----------------|--------------------|
| SnO <sub>2</sub> /Perovskite                   | 3.73          | 29.74          | 19.81         | 70.26          | 18.62              |
| SnO <sub>2</sub> -SnS <sub>2</sub> /Perovskite | 1.65          | 49.64          | 16.56         | 50.36          | 15.23              |

$\tau_{avg.}$  are calculated by using the equation of  $\tau_{avg.} =$

Table S4 Summary of the device performance based on metal sulfide ETLs.

| Year       | Materials                          | V <sub>oc</sub> (V) | J <sub>sc</sub> (mA/cm <sup>2</sup> ) | FF (%) | PCE (%) | Ref. |
|------------|------------------------------------|---------------------|---------------------------------------|--------|---------|------|
| 2018       | CBD CdS                            | ~0.95               | ~18.0                                 | ~50.0  | ~10%    | [1]  |
| 2018       | sputtered CdS                      | 1.10                | 20.71                                 | 58.0   | 13.17%  | [2]  |
| 2019       | MoS <sub>2</sub>                   | 0.89                | 21.7                                  | 63.8   | 12.68%  | [3]  |
| 2020       | 2H-TaS <sub>2</sub>                | 0.94                | 22.5                                  | 66.2   | 14.82%  | [4]  |
| 2020       | 2H-WS <sub>2</sub>                 | 1.12                | 22.24                                 | 0.731  | 18.21%  | [5]  |
| 2018       | SnS <sub>2</sub> Arrays            | 0.95                | 23.70                                 | 66.1   | 13.63%  | [6]  |
| 2018       | Exploited SnS <sub>2</sub>         | 1.161               | 23.55                                 | 73     | 20.12%  | [7]  |
| 2019       | Evaporated SnS <sub>2</sub>        | 1.011               | 21.70                                 | 60.0   | 13.2%   | [8]  |
| 2020       | SnS <sub>2</sub> /SnS              | 1.08                | 23.27                                 | 72.0   | 18.08%  | [9]  |
| 2021       | TiS <sub>2</sub> -TiO <sub>2</sub> | 1.13                | 22.4                                  | 75.2   | 18.73%  | [10] |
| this study | SnS <sub>2</sub> nanosheet         | 1.09                | 22.7                                  | 74.9   | 18.5%   | —    |
| this study | SnO <sub>2</sub> -SnS <sub>2</sub> | 1.14                | 23.7                                  | 79.2   | 21.5%   | —    |

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